

ABSTRACT OF THE DISCLOSURE

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In a semiconductor photo-detector of the present invention, a first semiconductor layer, a second
5 semiconductor layer having, and a photo-absorption part composed of a photo-absorption layer sandwiched between these layers are disposed on a substrate, at least the photo-absorption layer is formed at a position apart inwardly by a finite length from an
10 end surface of the substrate, an end surface of the second semiconductor layer and the substrate or the end surface of the substrate is provided with a light incident facet angled inwardly as it separates from the surface of the second semiconductor or the
15 surface of the substrate. Further, a groove as a guide of an optical waveguide for guiding incident light is disposed opposing the light incident facet, or the substrate end surface at the light incident facet side is protruded by a finite length from a
20 tip part of the light incident facet, or between the optical waveguide and the semiconductor photo-detector is buried in a solid or liquid, or a main reaching area of incident light refracted at an upper layer of the photo-absorption layer is
25 terminated with a substance having a smaller refractive index than the semiconductor layer of

photo-absorption region part, or the light incident
facet and its vicinity are buried in an organic
substance.

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